

TOSHIBA Photointerrupter Infrared LED + Phototransistor

TLP830(F)

Lead(Pb)-Free

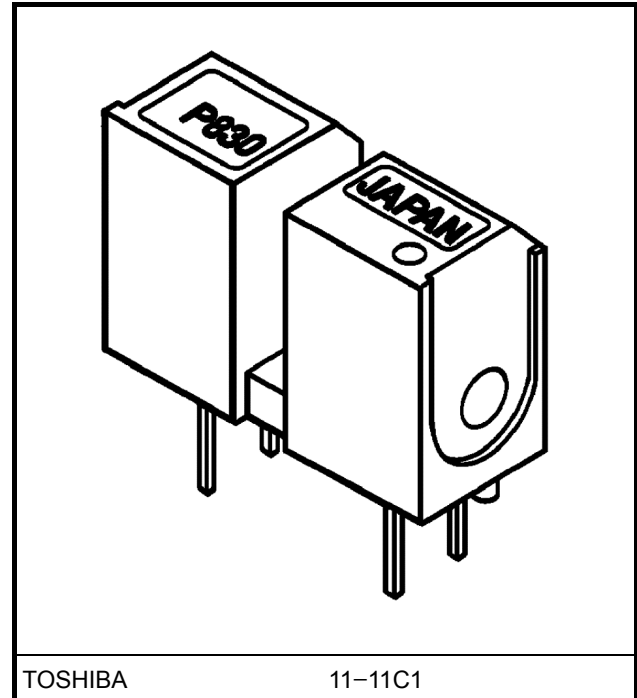
Track "00" Sensor For Floppy Disk Drive

Detection Of Sub-Scanning Quantity By Image Scanner

Various Position Detection Sensor

TLP830(F) is a photointerrupter which uses a high-radiant power GaAs LED and a fast-response Si phototransistor. The device is high resolution with a narrow slit pitch.

- Small package: 7.4mm (H), 4.5mm (D)
- Printed wiring board direct mounting type (with a locating pin).
- Board thickness: 1mm or less
- Short lead type enabling automated mounting
- Gap: 2mm
- High resolution: Slit width 0.15mm
- High current transfer ratio: $I_C/I_F = 3\%$ (min)
- Material of the package
: Polybutylene terephthalate (UL94V-0, black color)
- Detector side is of visible light cut type.



TOSHIBA 11-11C1

Weight: 0.4 g (typ.)

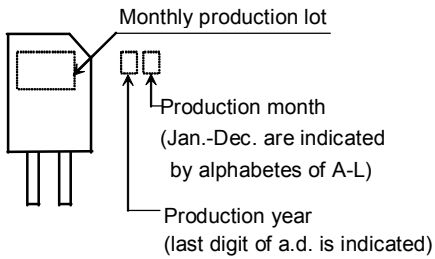
Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
LED	Forward current	I_F	50	mA	
	Forward current derating	$\Delta I_F / ^\circ\text{C}$	Ta > 25°C	-0.33	
			Ta > 85°C	-2	
Reverse voltage		V_R	5	V	
Detector	Collector-emitter voltage		V_{CEO}	35	V
	Emitter-collector voltage		V_{ECO}	5	V
	Collector power dissipation		P_C	75	mW
	Collector power dissipation derating (Ta > 25°C)		$\Delta P_C / ^\circ\text{C}$	-1	mW / °C
	Collector current		I_C	50	mA
Operating temperature range		T_{opr}	-30~85	°C	
Storage temperature range		T_{stg}	-40~100	°C	
Soldering temperature (5 s)		T_{sol}	260	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Product Indication



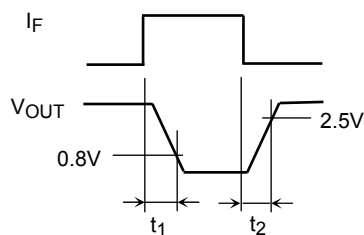
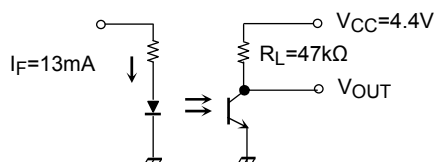
Operating Ranges

Characteristic	Symbol	Min	Typ.	Max	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	I_F	—	—	25	mA
Operating temperature	T_{opr}	-10	—	75	°C

Opto Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit	
LED	Forward voltage	V_F	$I_F = 10 \text{ mA}$	1.00	1.15	1.30	V	
	Reverse current	I_R	$V_R = 5 \text{ V}$	—	—	10	μA	
	Peak emission wavelength	λ_P	$I_F = 10 \text{ mA}$	—	940	—	nm	
Detector	Dark current	I_D	$V_{CE} = 24 \text{ V}, I_F = 0$	—	—	0.1	μA	
	Peak sensitivity wavelength	λ_P		—	870	—	nm	
Coupled	Current transfer ratio	I_C/I_F	$V_{CE} = 2 \text{ V}, I_F = 10 \text{ mA}$	3	—	20	%	
	Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_F = 20 \text{ mA}, I_C = 0.3 \text{ mA}$	—	0.1	0.35	V	
	Switching times	Rise time	t_r	$V_{CC} = 5 \text{ V}, I_C = 1 \text{ mA}$	—	15	—	μs
		Fall time	t_f	$R_L = 1 \text{ k}\Omega$	—	15	—	
		Response time (1)	t_1	$V_{CC} = 4.4 \text{ V}, I_C = 13 \text{ mA}$	—	—	80	
Response time (2)		t_2	$R_L = 47 \text{ k}\Omega$ (Note)	—	—	800		

Note: t_1, t_2 test condition

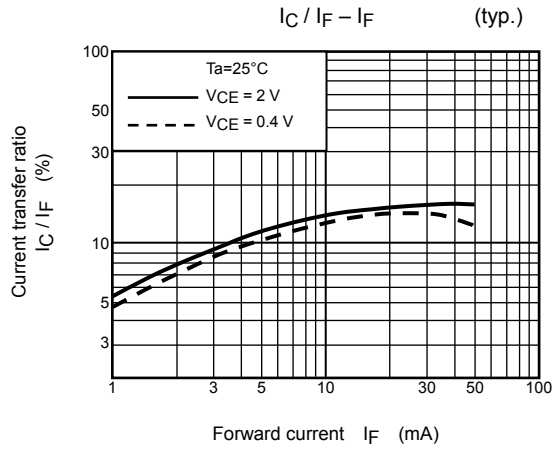
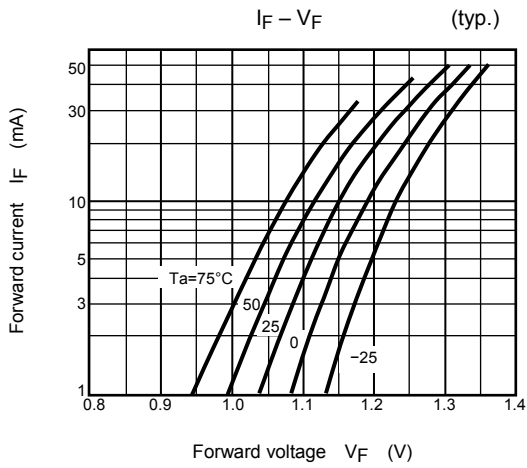
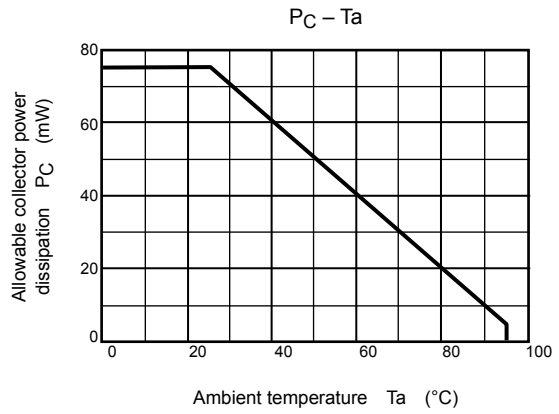
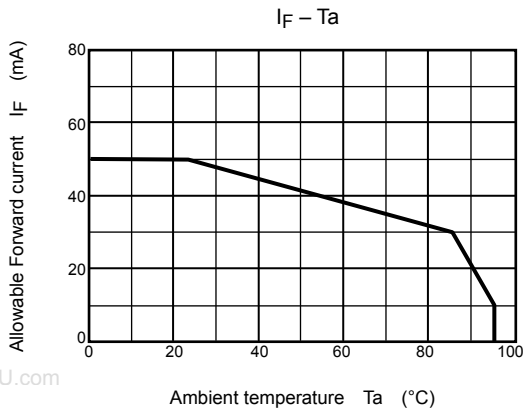


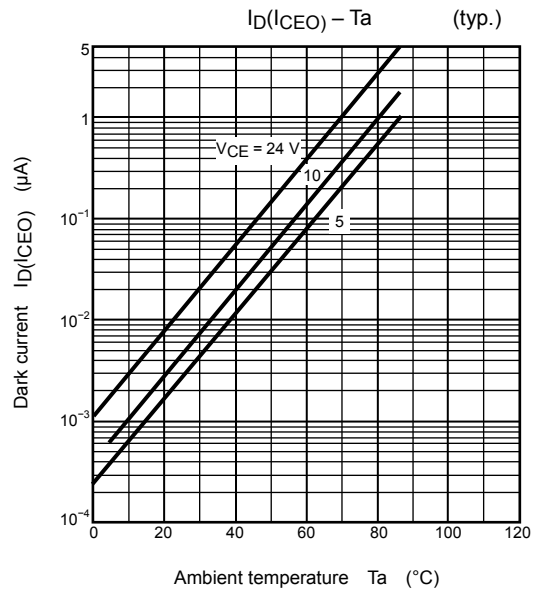
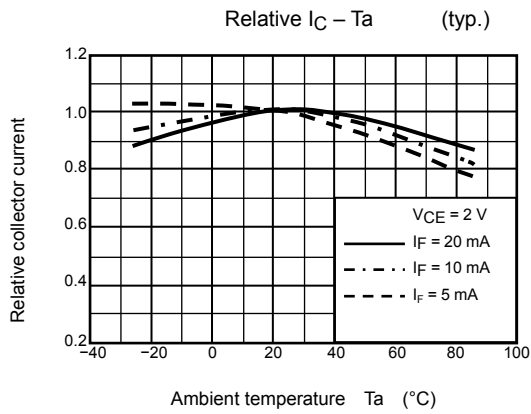
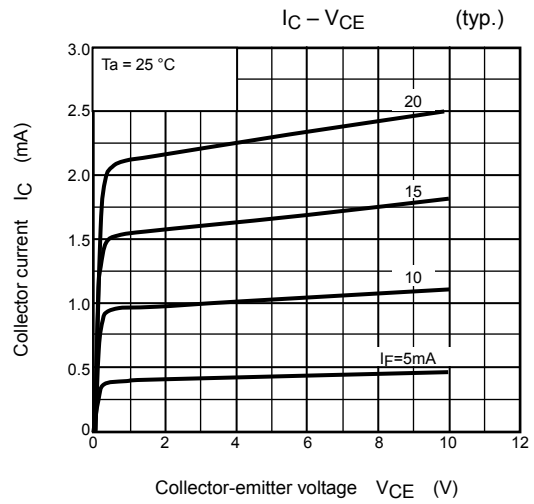
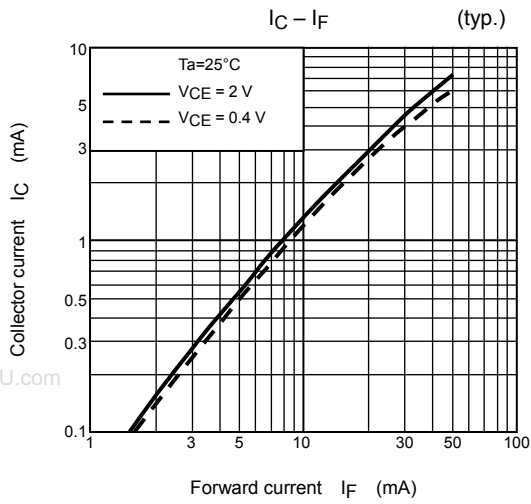
Precaution

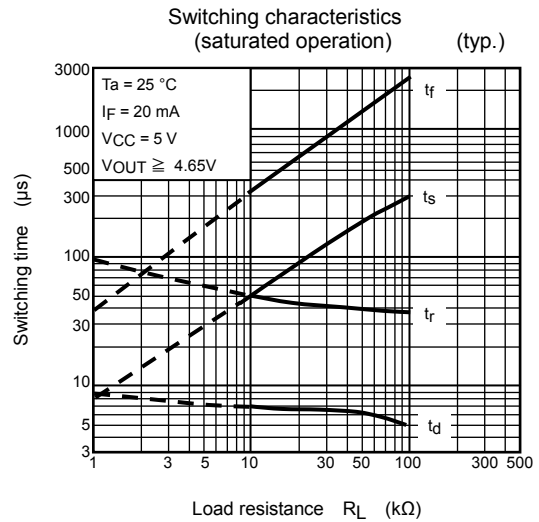
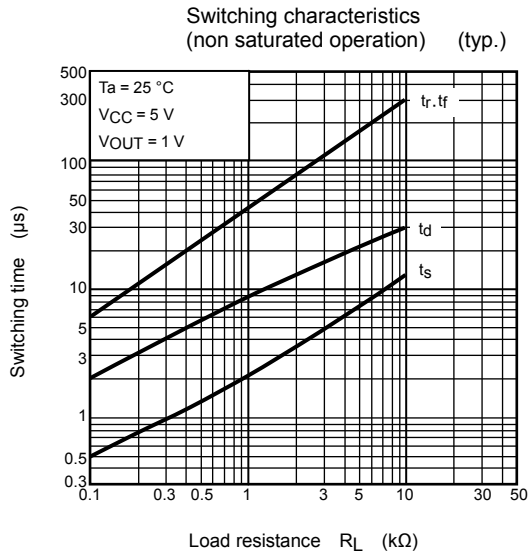
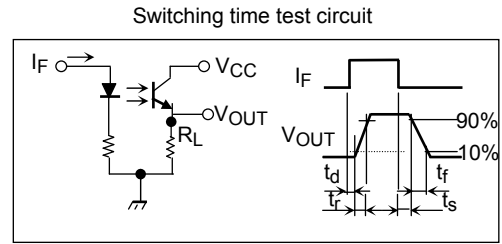
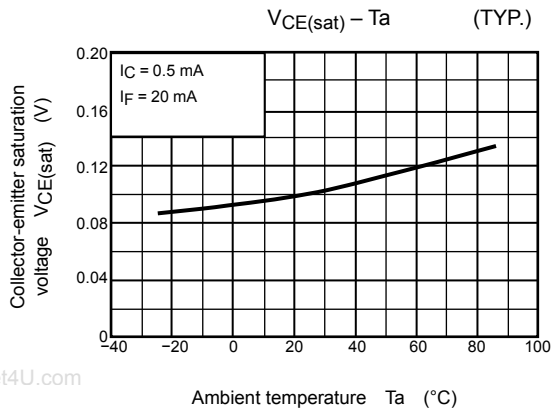
1. If the chemical are used for cleaning, the soldered surface only shall be cleaned with chemicals avoiding the whole cleaning of the package.
2. The container is made of polybutylene terephthalate. Oil or chemicals may cause melting or cracks. Check the environment carefully before installing.
3. Shall be mounted on an unwarped surface.
4. A visible light cut-off type photo transistor which blocks light with frequencies of 700nm or above is used. However, the device cannot block ambient light with a wavelength of 700nm or more or sunlight. Install avoiding the disturbance light.
5. Conversion efficiency falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in conversion efficiency over time. The ratio of fluctuation in conversion efficiency to fluctuation in infrared LED optical output is 1: 1.

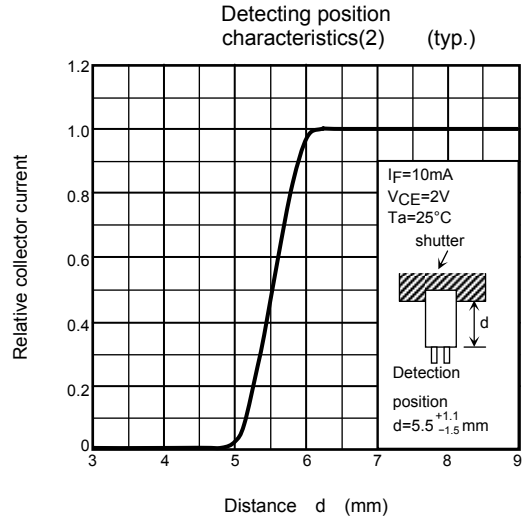
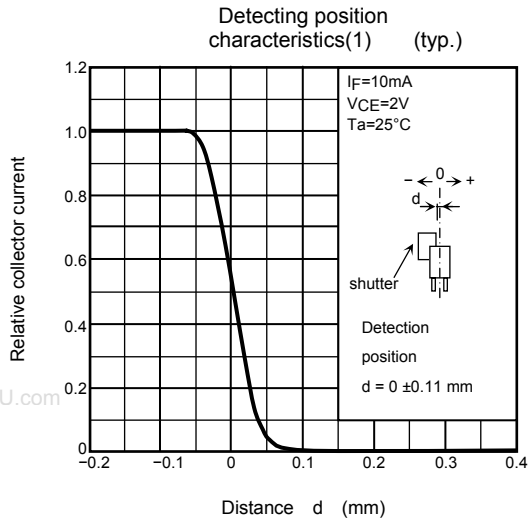
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$$\frac{I_C / I_F(t)}{I_C / I_F(0)} = \frac{P_O(t)}{P_O(0)}$$



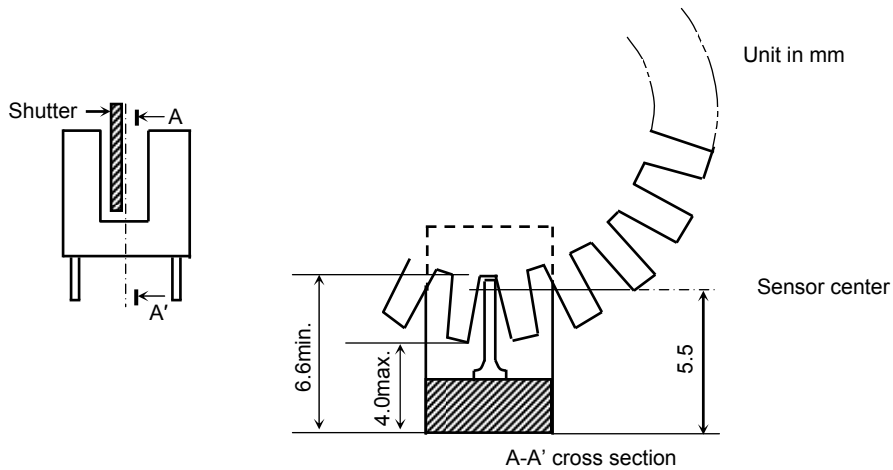






Positioning Of Shutter And Device

To operate correctly, make sure that the shutter and the device are positioned as shown in the figure below. The slit pitch of the shutter must be set wider than the slit width of the device. Determine the width taking the switching time into consideration.



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20070701-EN

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